In the Claims:

1. (Currently Amended) A method of fabricating a high dielectric constant (high-k) capacitor structure, said method comprising:

depositing an adhesion layer in physical contact with a SiO_2 substrate, said adhesion layer being selected from the group consisting of at least one of Si,[[,]] and IrO_2; and

depositing a noble metal bottom electrode in physical contact with said adhesion layer.

2. (Original) The method of claim 1 further comprising:

depositing a high-k dielectric material on said bottom electrode;

depositing a top electrode on said high-k dielectric layer;

patterning said top electrode and said high-k diclectric layer;

depositing an insulation layer thereon;

opening vias to said top electrode in the insulation layer;

depositing a metal pad layer in said vias and atop said insulation layer; and

patterning the metal pad layer.

3. (Currently Amended) The method recited in claim 1 wherein said noble metal bottom electrode is Pt.

4. (Original) The method recited in claim 2 wherein said top electrode is Pt.

5. (Original) The method recited in claim 2 wherein said insulation layer is SiO_2.

6. (Original) The method recited in claim 2 wherein said metal pad layer is Al or W.

7-15. (Canceled)

16. (Previously Presented) The method of Claim 1, wherein the step of depositing an adhesion layer on the SiO_2 substrate comprises depositing a conductive layer.

17. (Currently Amended) The method of Claim [[17]] 16, wherein the step of depositing a conductive layer comprises depositing a layer of IrO_2.

18-20. (Canceled)

21. (Currently Amended) The method of Claim 16, wherein the step of ~~wherein the step of~~ depositing a noble metal bottom electrode comprises depositing Pt.

22-28. (Canceled)